

# Hybrid Bonding: To Be or Not To Be?

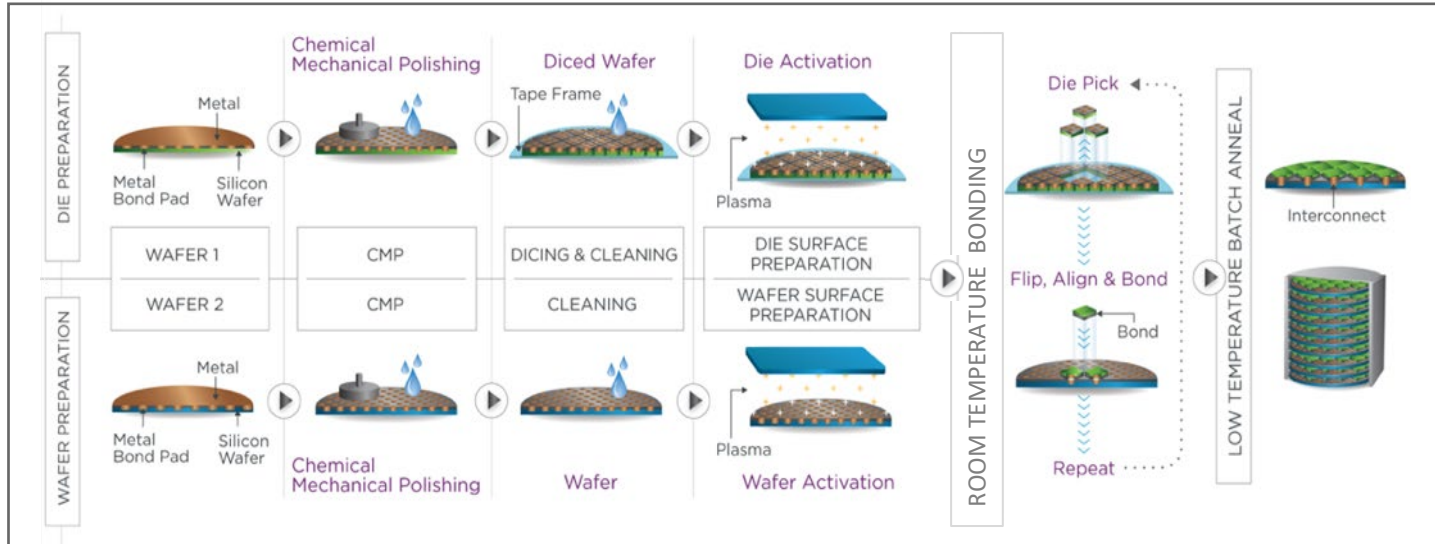
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# Key Metrology for Improved Yield and Throughput



## Must Haves

- Reliable metrology tuned to performance
- Establish a “health of the line” protocol for all process steps

## Wants

- Improved Nanoscale Topography<sup>1</sup>  
(KGD processes more sampling/higher yield)  
Accurate & Fast for High Volume  
Interferometry ~1000x Faster than AFM<sup>1</sup>  
Fine pitch (optical techniques and accuracy)
- Surface Defect Detection<sup>2</sup>  
Large-area automated detection: ML

## Stretch Goal

- Rework Hybrid Bonding  
High-cost Die / Stack Replacement  
Bond Energy Engineering

### Assumptions

- High yield BEOL
- Lithography
- Etch
- Plate

### Pre- Bond Metrology

- Surface Topography<sup>1,2</sup>
- Surface Defects<sup>3</sup>
- Grain Structure
- Wafer and Die Warp

### Post Bond Metrology

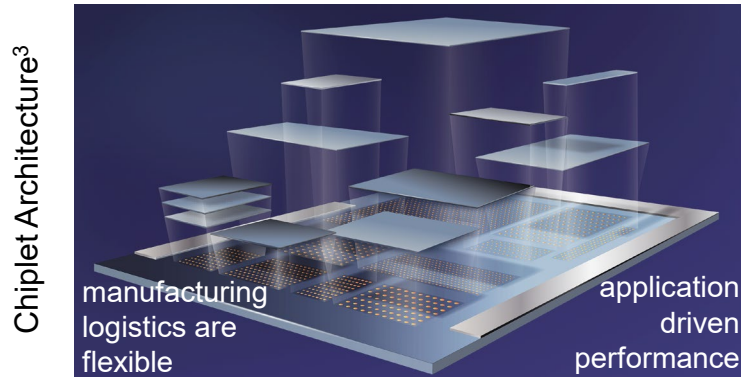
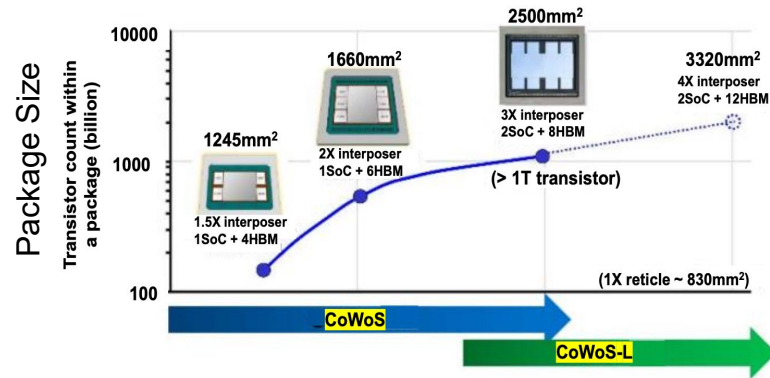
- Bond Energy<sup>4</sup>
- Bond Voids
- Electrical Connectivity

1. Bongsub Lee et al., “High-Throughput Characterization of Nanoscale Topography for Hybrid Bonding by Optical Interferometry,” ECTC 2024.  
 2. Bongsub Lee et al., “Nanoscale Topography Characterization for Direct Bond Interconnect,” ECTC 2019.  
 3. Oliver Zhao et al., “Deep Convolution Neural Networks for Automatic Detection of Defects which Impact Hybrid Bonding Yield,” ECTC 2024.  
 4. Bongsub Lee et al., “Mechanical Strength Characterization of Direct Bond Interfaces for 3D-IC and MEMS Applications,” ECTC 2018  
 5. G. Gao and L. Mirkarimi, “Hybrid Bonding Process-Ch. 3; *Direct Cu Bond Interconnection for Advanced Semiconductor Technology*, edited by Dongkai Shangguan CRC Press, 2024.

# 2.5 & 3.5D Packaging Evolution with Hybrid Bonding

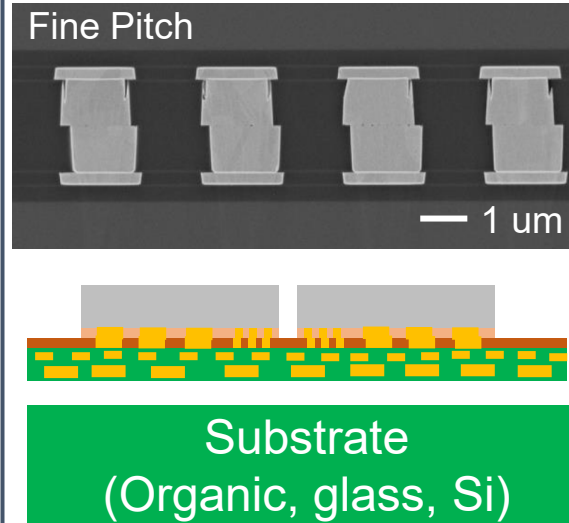
## Package Trends

- Package size is >3x reticle size.<sup>1</sup>
- Heterogenous integration with high I/O density
- Chiplet architecture for application optimization

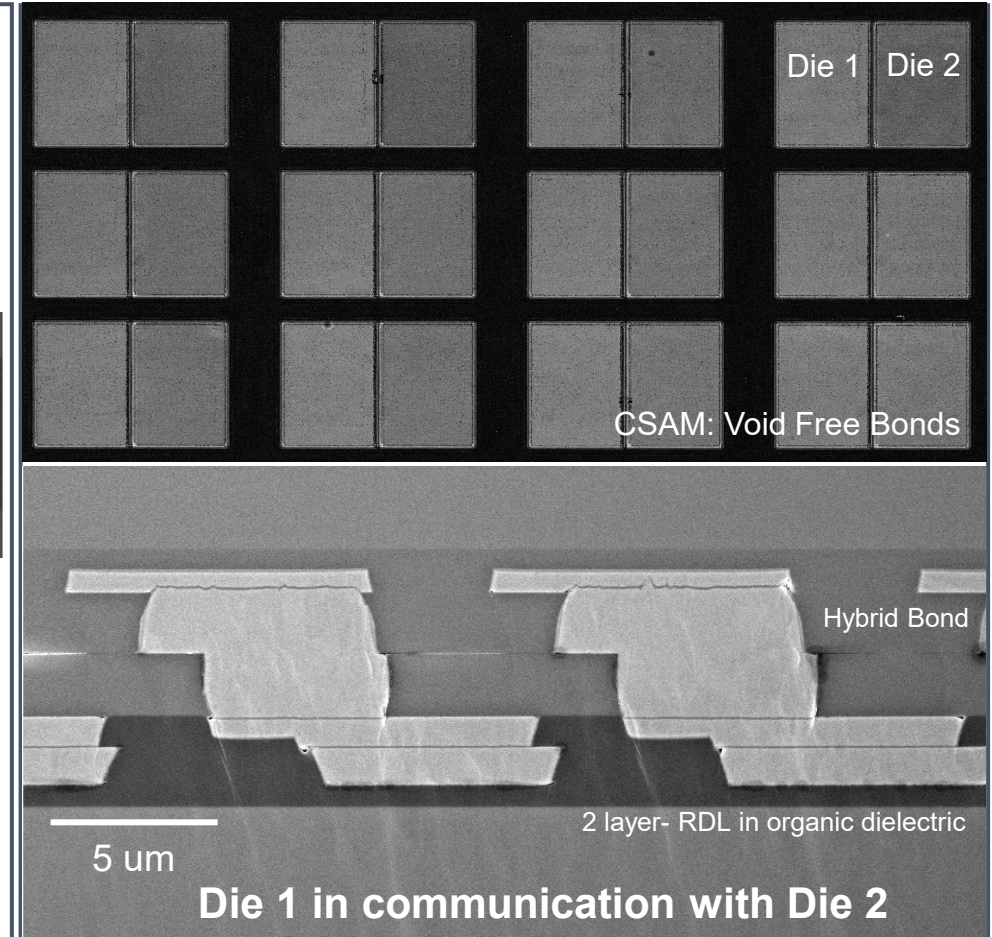


## Solving Challenges

- Ultra-high bandwidth, inter-die communication with D2W pitch down to 1 $\mu$ m.<sup>2</sup>
- System simplification
  - Bond die directly to substrate
  - Bridge die replace interposer



## Hybrid Bonded Die to Organic RDL<sup>4</sup>



1. Hu, et al, "CoWoS Architecture Evolution for Next Generation HPC on 2.5D System in Package", ECTC 2023.

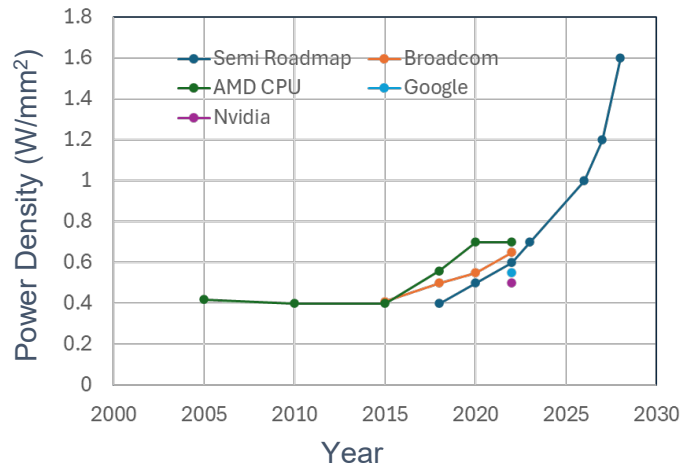
2. Theil, et al, "Recent Development in Fine Pitch W2W Hybrid Bonding with Cu Interconnect", IWLPAC 2019.

3. L. Mirkarimi et al, "Hybrid Bonding Technology for Chiplets", Tutorial Session C, Chiplet Summit 2022, Santa Clara, January 2022.

4. Adeia, unpublished.

## The Challenge

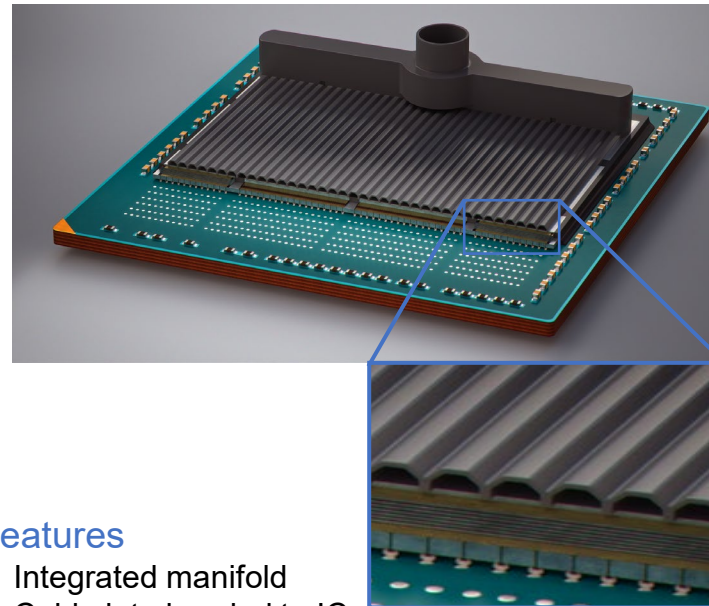
### Power Density Roadmap



- AI workflows and large language models are driving the high-power densities in ICs.
- New cooling technologies are emerging (micro-jetting, immersion, and others...) <sup>1,2</sup>

## Hybrid & Direct Bonding Solutions

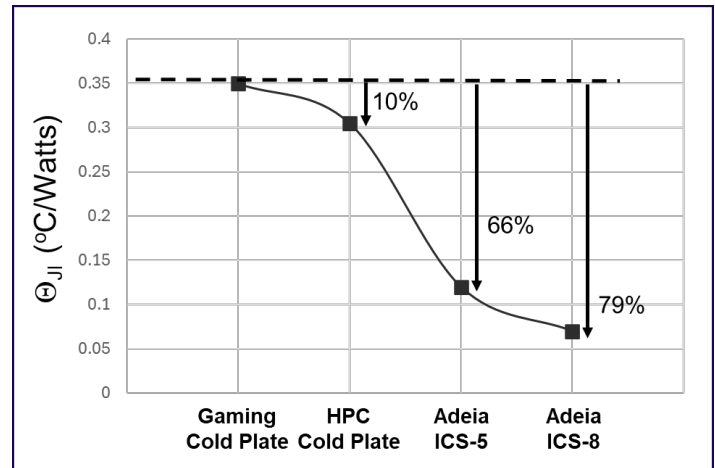
### Integrated Cooling Solution<sup>3,4</sup>



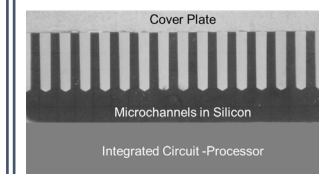
### Features

- Integrated manifold
- Cold plate bonded to IC
- Eliminate TIM, reduce thermal resistance
- Inexpensive fab process
- Custom design to manage heat map
- Improved thermal performance design
- Tested to 3W/mm<sup>2</sup> power density

### Thermal Resistance Reduction



Improved performance over standard TIM based solutions: Gaming and HPC cold plates had silver based and PTM7950 TIMs, respectively.



Early μchannels<sup>5</sup> issues solved with this approach.  
-excessive pressure drop  
-integration

- M. Walsh, et al., "Embedded microjets for thermal management of high power-density electronic devices", IEEE Trans. Compts, Pckg. and Man.Tech., vol. 9, no.2, pp. 269–278, Feb. 2019.
- L.J. Lieu et al, "An Energy-efficient Si-integrated Micro-cooler for High Power and Power-density Computing Applications", ECTC, p.1025-1029. May 2024.
- R,Zhang et al, "Revolutionary Cooling Solution for Hot Chips", iTherm 2025, May 26<sup>th</sup> (2025); Session TII-06, Tate Ballroom A2 (11AM)
- Adeia Booth- ECTC 2025, Booth # 308.
- D.B.Tuckerman and R.F.W. Pease, IEEE Electronic Device Letters, EDL-2, No. 5, May 1981.